

ZXMN10A07F

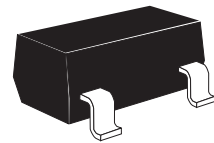
100V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 100V$; $R_{DS(ON)} = 1\Omega$ $I_D = 0.64A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



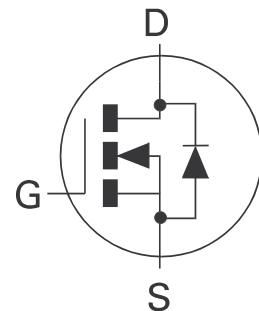
SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Relay and Solenoid driving
- Motor control

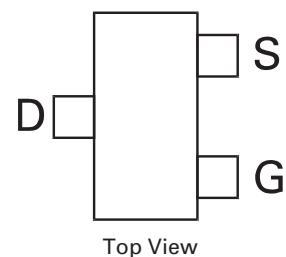


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN10A07FTA	7"	8mm	3000 units
ZXMN10A07FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N1



ZXMN10A07F

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$; $T_A=25^{\circ}C$ (a)	I_D	0.64 0.51 0.56	A
Pulsed Drain Current (c)	I_{DM}	2.5	A
Continuous Source Current (Body Diode) (b)	I_S	2	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	2.5	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^{\circ}C/W$

NOTES

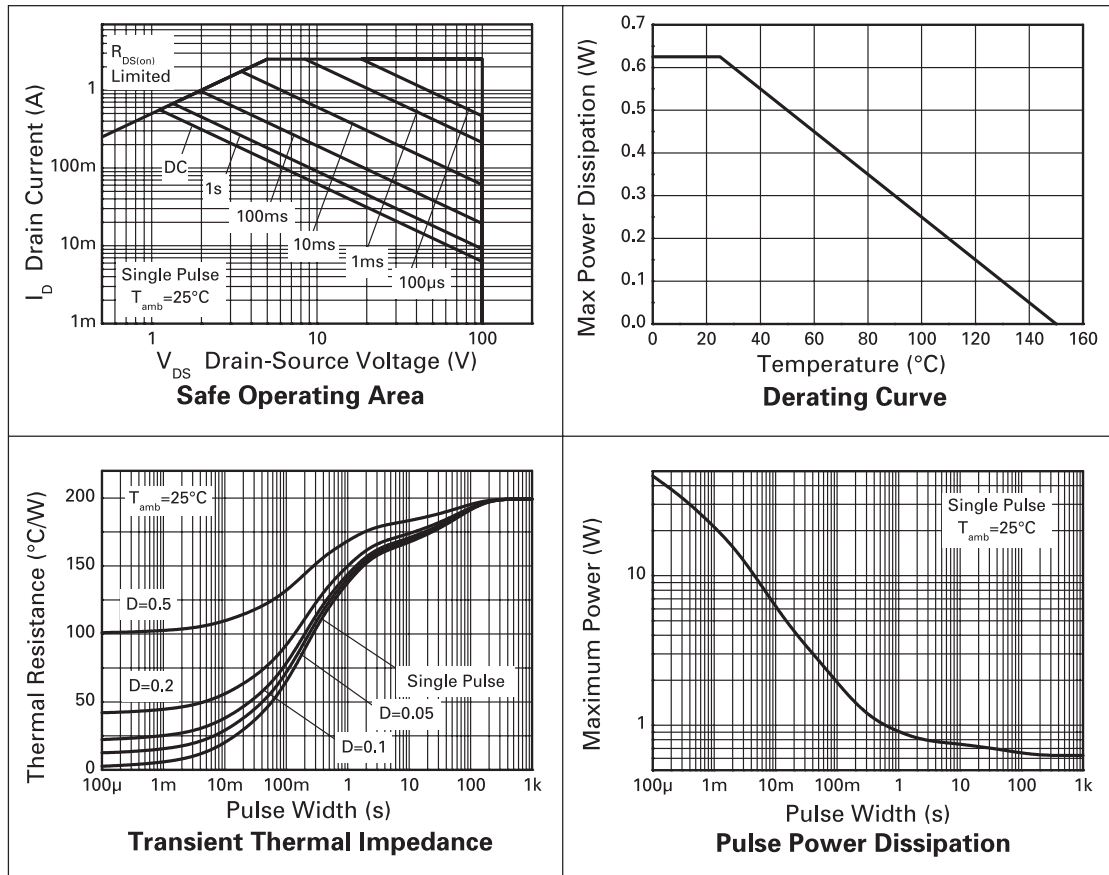
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$, pulse width 10 μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

ZXMN10A07F

CHARACTERISTICS



ZXMN10A07F

ELECTRICAL CHARACTERISTICS (at TA = 25°C unless otherwise stated)

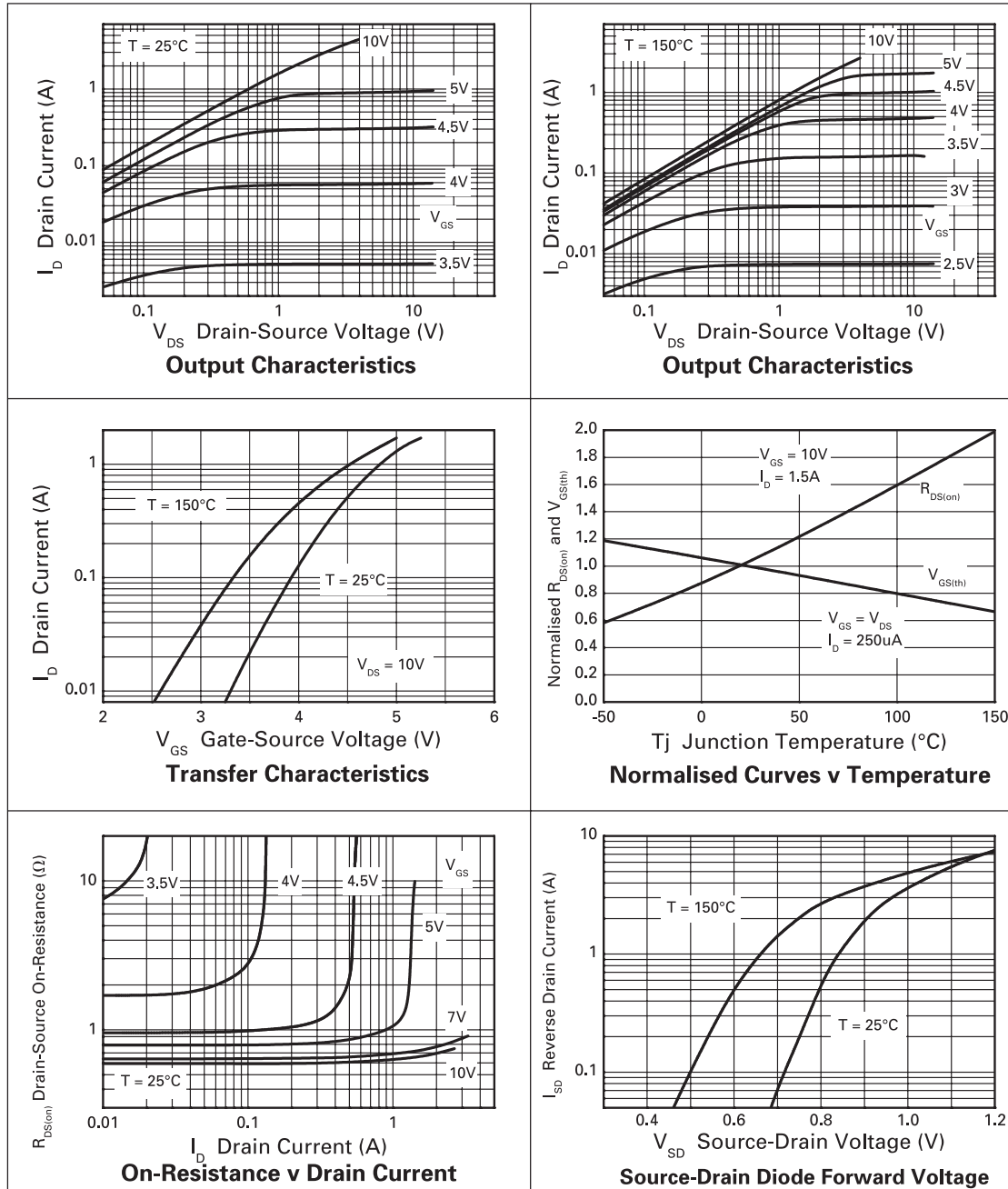
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V(BR)DSS	100			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	2.0		4.0	V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			1 1.1	Ω Ω	V _{GS} =10V, I _D =1.5A V _{GS} =6V, I _D =1A
Forward Transconductance (3)	g _{fs}		1.6		S	V _{DS} =15V,I _D =1A
DYNAMIC (3)						
Input Capacitance	C _{iss}		138		pF	V _{DS} =60 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		12		pF	
Reverse Transfer Capacitance	C _{rss}		6		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.8		ns	V _{DD} =50V, I _D =1A R _G =6.0Ω, V _{GS} =10V
Rise Time	t _r		1.5		ns	
Turn-Off Delay Time	t _{d(off)}		4.1		ns	
Fall Time	t _f		2.1		ns	
Total Gate Charge	Q _g		2.9		nC	V _{DS} =50V,V _{GS} =10V, I _D =1.0A
Gate-Source Charge	Q _{gs}		0.7		nC	
Gate-Drain Charge	Q _{gd}		1		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _J =25°C, I _S =1.5A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		27		ns	T _J =25°C, I _F =1.8A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		12		nC	

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu s$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

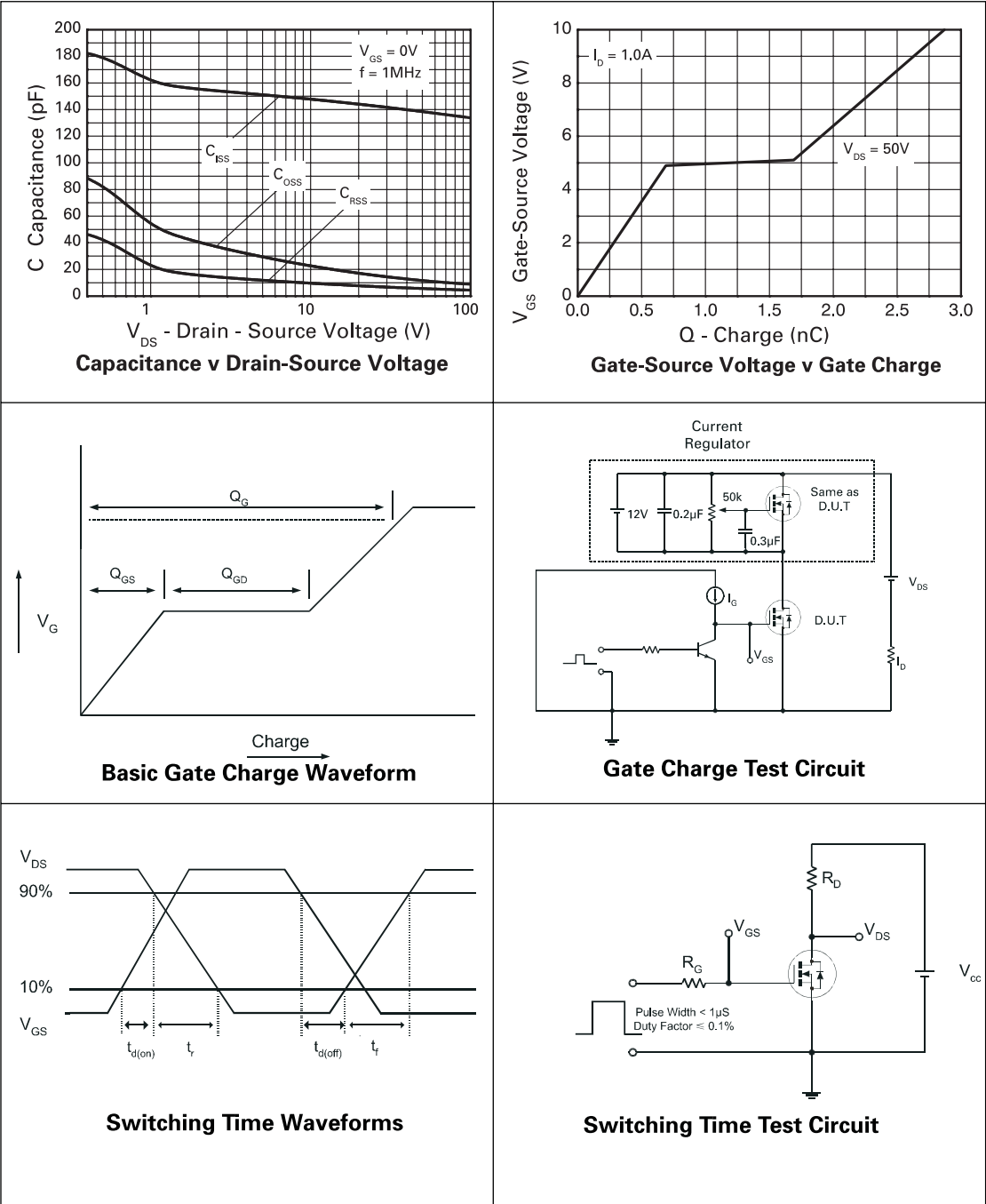
ZXMN10A07F

TYPICAL CHARACTERISTICS



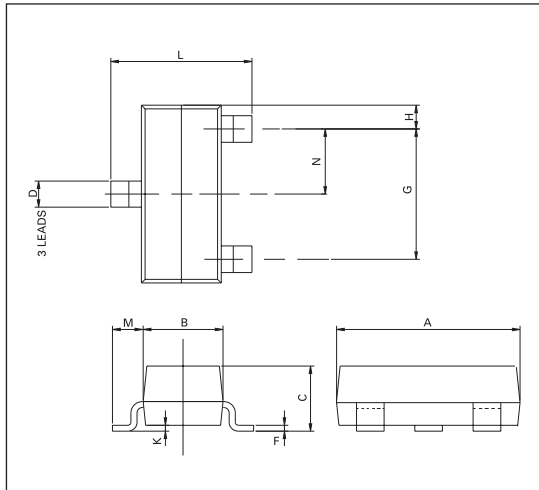
ZXMN10A07F

TYPICAL CHARACTERISTICS

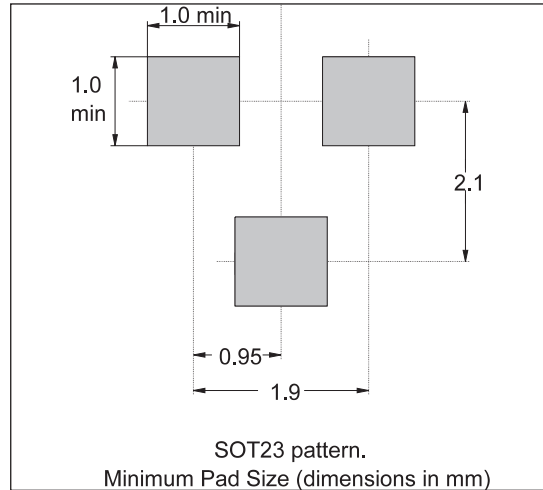


ZXMN10A07F

PACKAGE OUTLINE



PAD LAYOUT



PACKAGE DIMENSIONS

DIM	MILLIMETRES		DIM	MILLIMETRES	
	MIN	MAX		MIN	MAX
A	2.67	3.05	H	0.33	0.51
B	1.20	1.40	K	0.01	0.10
C	—	1.10	L	2.10	2.50
D	0.37	0.53	M	0.45	0.64
F	0.085	0.15	N	0.95 NOM	
G	1.90 NOM		φ	10° TYP	

© Zetex plc 2002

Zetex plc
Fields New Road
Chadderton
Oldham, OL9 8NP
United Kingdom
Telephone (44) 161 622 4422
Fax: (44) 161 622 4420

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany
Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49

Zetex Inc
700 Veterans Memorial Hwy
Hauppauge, NY11788
USA
Telephone: (631) 360 2222
Fax: (631) 360 8222

Zetex (Asia) Ltd
3701-04 Metroplaza, Tower 1
Hing Fong Road
Kwai Fong
Hong Kong
Telephone: (852) 26100 611
Fax: (852) 24250 494

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com

ISSUE 1 - MARCH 2002

